Supporting information

Multi-scale carbon@Sb mesoporous composites activated by in-situ localized electrochemical pulverization as highrate and long-life anode materials for potassium-ion batteries

Jie Ren¹, Xiang Wang¹, Jihao Li², Qianzi Sun¹, Shaozhou Li¹, Ling Bai¹, Xianming Liu³, Guilong Liu³, Ziquan Li¹,* Haijiao Zhang²,* Zhen-Dong Huang^{1,*}

State Key Laboratory for Organic Electronics and Information Displays
& Jiangsu Key Laboratory for Biosensors, Institute of Advanced Materials,
Jiangsu National Synergetic Innovation Center for Advanced Materials,
Nanjing 210023, P. R. China

2. Institute of Nanochemistry and Nanobiology, School of Environmental and Chemical Engineering, Shanghai University, Shanghai 200444, P. R. China

3. College of Chemistry and Chemical Engineering, Luoyang Normal University, Luoyang, Henan, 471934, P. R. China

*Corresponding authors: <u>iamzdhuang@njupt.edu.cn</u> (Z. D. Huang); <u>lizq@njupt.edu.cn</u> (Z. Q. Li); <u>hjzhang128@shu.edu.cn</u> (H. J. Zhang)

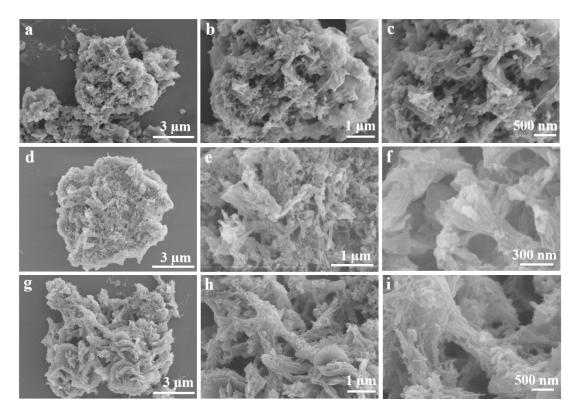


Figure S1. SEM images in different magnifications of samples: (a-c) Sb₂@DCDA/PACP, (d-f) Sb₃@DCDA/PACP, and (g-i) Sb₄@DCDA/PACP.

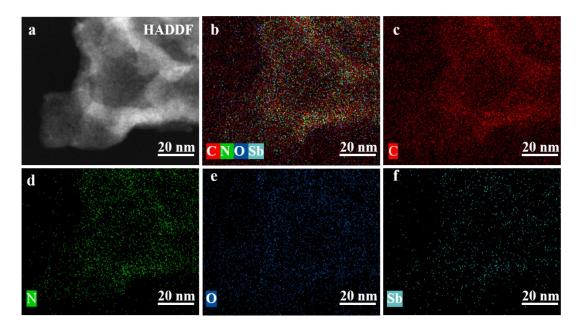


Figure S2. (a) HAADF image of Sb₃@HCNS, and (b-f) combined and individual elemental distribution maps of C, N, O, and Sb.

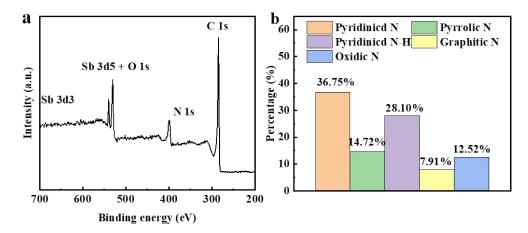


Figure S3. (a) X-ray photoelectron spectroscopy (XPS) full spectrum of Sb₃@HCNS, (b) The fraction of pyridinic N (398.2 eV), pyrrolic N (399.6 eV), pyridinic N-H (400.7 eV), graphitic N (401.5 eV), and oxidized N (403.5 eV) within N 1s spectrum in Figure 3f.

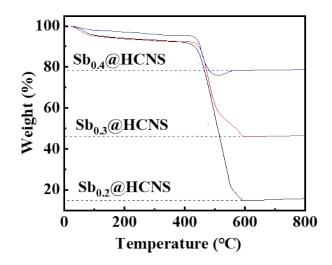


Figure S4. Thermogravimetry (TG) curves of as-prepared Sb₂@HCNS, Sb₃@HCNS, and Sb₄@HCNS.

The weight loss of carbon combustion and the weight gain of Sb_2O_4 formation based on the following reactions:

(1) C+O₂=CO₂;

(2)
$$2Sb+2O_2=Sb_2O_4$$
.

The weight ratio of Sb in the nanocomposite can be calculated based on the following equation:

Equation S1

 $\frac{121.76}{\text{Sb}_2 \text{@HCNS: } S(wt.\%)} = \frac{121.76}{307.52 \times} \frac{15.1}{100 \times 2 \times 100\%} = 11.96\%$

 $Sb_{3}@HCNS: S(wt.\%) = \frac{121.76}{307.52} \times \frac{45.9}{100} \times 2 \times 100\% = 36.35\%$ $\frac{121.76}{100} \times \frac{78.5}{100}$

Sb₄@HCNS: $S(wt.\%) = \overline{307.52} \times \overline{100} \times 2 \times 100\% = 62.16\%$

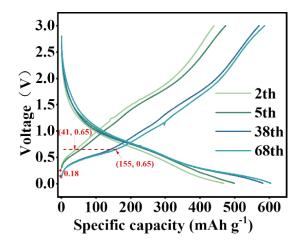


Figure S5. The discharge/charge profiles of Sb₃@HCNS at the 2nd, the 5th, the 38th and the 68th cycle at the current density of 0.1 A g⁻¹ during the rate capability testing.

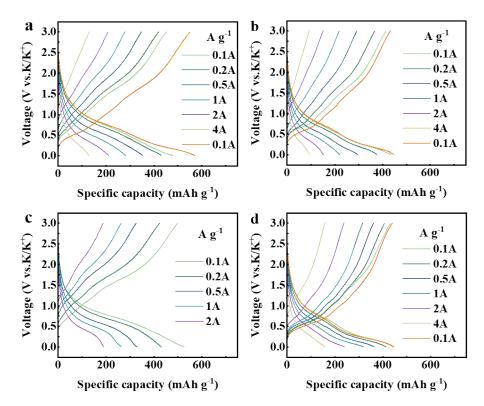


Figure S6. The typical charge/discharge profiles of (a) Sb₂@HCNS, (b) Sb₃@HCNS, (b) Sb₄@HCNS at various current densities at 2nd, 7th, 12th, 17th, 22nd, 27th and 32nd, respectively. (d) The corresponding discharge/charge profiles of Sb₂@HCNS at 38th, 43rd, 48th, 53rd, 58th, and 63rd.

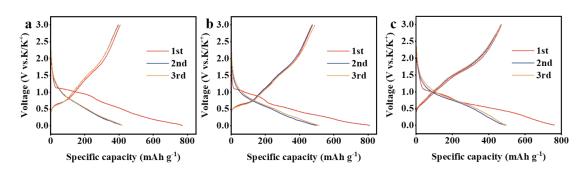


Figure S7. The discharge/charge profiles of Sb₂@HCNS (a), Sb₃@HCNS (b), and Sb₄@HCNS (c) at the current density of 0.1 A g^{-1} during the initial three activation cycles before long-term cyclic testing at 2 A g^{-1} .

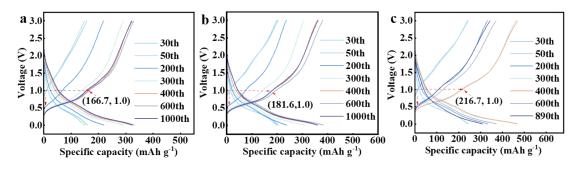


Figure S8. The different cycle discharge/charge profiles of $Sb_2@HCNS$ (a), $Sb_3@HCNS$ (b), and $Sb_4@HCNS$ (c) at the current density of 2 A g⁻¹ during the long-term cyclic testing.

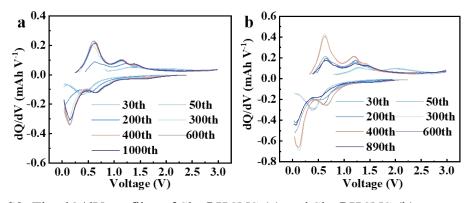


Figure S9. The dQ/dV profiles of Sb₂@HCNS (a) and Sb₄@HCNS (b) corresponding to the different cycle discharge/charge profiles at the current density of 2 A g^{-1} during the long-term cyclic testing shown in Figures S7a and S7c.

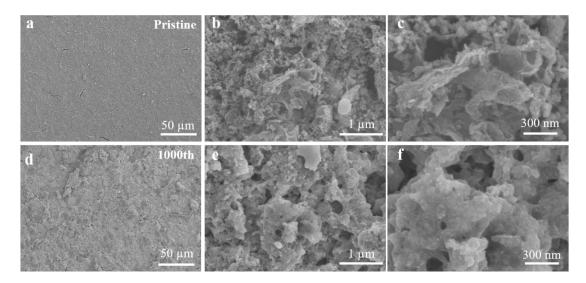


Figure S10. SEM images of (a-c) pristine $Sb_3@HCNS$ electrode, and (d-f) the $Sb_3@HCNS$ electrode being cycled for 1000 cycles at 2 A g⁻¹.

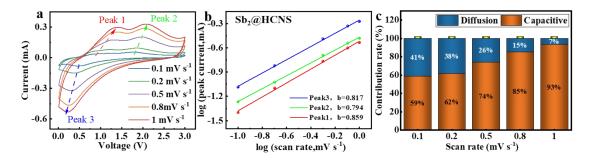


Figure S11. (a) CV curves of Sb₂@HCNS at various scan rates from 0.1 to 1.0 mV s⁻¹. (b) The plot of log (peak current) versus log (scan rate) of redox peaks from CV curves and b-value determination lines. (c) Contribution ratios of the surface capacitance and inside diffusion-based capacity to the total capacity of Sb₂@HCNS at different scan rates.

The contributions of the surface-controlled and diffusion-controlled reactions were quantitatively estimated based on the redox peak currents of CV curves according to the equation: $i = av^b$. Normally, the peak current, i, is proportional to the sweep rate, v. The b value was determined from the plot slope of the log (i) versus log (v). When the b value is 1, the electrochemical reaction is purely surface-controlled. when the b value is 0.5, the electrochemical reaction is entirely diffusion-controlled. The surface-controlled (*k1v*) and diffusion-controlled ($k_2v^{1/2}$) contribution to final capacity can be divided into components according to the equation: $i = k_1v + k_2v^{1/2}$ [1].

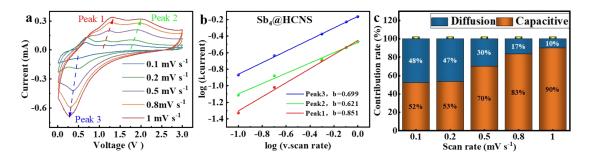


Figure S12. (a) CV curves of Sb₄@HCNS at various scan rates from 0.1 to 1.0 mV s⁻¹. (b) The plot of log (peak current) versus log (scan rate) of redox peaks from CV curves and b-value determination lines. (c) Contribution ratios of the surface capacitance and inside diffusion-based capacity to the total capacity of Sb₄@HCNS at different scan rates.

303@110115.		
Element	Atomic fraction (%)	Mass fraction (%)
С	83.83	73.39
Ν	10.15	10.36
0	4.82	5.62
Sb	1.20	10.63

Table S1. HRTEM EDX analysis of C, N, O, Sb atomic and mass fraction in Sb₃@HCNS.

Table S2. XPS analysis of C, N, O, Sb atomic and mass fraction in Sb₃@HCNS.

Element	Atomic fraction (%)	Mass fraction (%)
С	71.15	56.26
Ν	13.73	12.67
0	12.95	13.65
Sb	2.17	17.42%

Materials	Cyclability (mAh g ⁻¹)	Rate performance (mAh g ⁻¹)	Ref.
		${\sim}447$ at 0.2 A g $^{-1}$	
		~419 at 0.4 A g ⁻¹	
Sb SQ@MA	~314 at 1 A g ⁻¹ after 1000 cycles	~366.4 at 0.8 A g ⁻¹	[37]
		~299 at 1.6 A g ⁻¹	
		\sim 246 at 3.2 A g ⁻¹	
		${\sim}379$ at 0.1 A g $^{-1}$	
		\sim 343 at 0.2 A g ⁻¹	
Sb-N-C	~254 at 1 A g ⁻¹ after 2000 cycles	\sim 302 at 0.5 A g ⁻¹	[39]
		~274 at 1 A g ⁻¹	
		\sim 245 at 2 A g ⁻¹	
		${\sim}576$ at 0.1 A g $^{-1}$	
O-Sb-N		${\sim}536$ at 0.2 A g $^{-1}$	
SA@NC2	~195 at 2A g-1 after 2000 cycles	\sim 312 at 0.5 A g ⁻¹	[41]
		~238 at 1 A g ⁻¹	
		~225 at 2 A g ⁻¹	
		~166 at 4 A g ⁻¹	
		~441 at 0.1 A g ⁻¹	
		~418 at 0.2 A g ⁻¹	
Sb SA/C	~331.3 at 1A g ⁻¹ after 1100	\sim 356 at 0.5 A g ⁻¹	[48]
	cycles	~312 at 1 A g ⁻¹	
		\sim 252 at 2 A g ⁻¹	
		${\sim}231.2$ at 0.1 A g ⁻¹	
		${\sim}205.7$ at 0.3 A g $^{-1}$	
NPS-FCM	\sim 162.1 at 1 A g ⁻¹ after	${\sim}190.4$ at 0.5 A g $^{-1}$	[49]
	1000cycles	${\sim}179.4$ at 1 A g $^{-1}$	
		~162.7 at 2 A g ⁻¹	
		~442.9 at 0.1 A g^{-1}	
		${\sim}420.2$ at 0.2 A $g^{\text{-1}}$	
HTSb@Sb ₂ O	${\sim}241.67$ at 2 A g $^{-1}$ after 2000	${\sim}361.4$ at 0.5 A g $^{-1}$	[50]
3@C	cycles	\sim 311.3 at 1 A g ⁻¹	
		\sim 273 at 2 A g ⁻¹	

Table S3. The performance comparison of $Sb_3@HCNS$ with the reported counterparts.

		${\sim}284$ at 0.1 A g $^{-1}$	
		~258 at 0.2 A g ⁻¹	
Mn-NC	\sim 146 at 1 A g ⁻¹ after 3000cycles	${\sim}240$ at 0.4 A $g^{\text{-1}}$	[51]
		${\sim}207$ at 0.8 A g $^{-1}$	
		~191 at 1 A g ⁻¹	
		${\sim}162$ at 2 A g $^{-1}$	
		~417 at 0.1 A g ⁻¹	
		\sim 329 at 0.2 A g ⁻¹	
Ni @BNHC	~279 at 1A g-1 after 1500cycles	${\sim}268$ at 0.5 A g $^{-1}$	[52]
		~215 at 1 A g ⁻¹	
		${\sim}154$ at 2 A g $^{-1}$	
		${\sim}230$ at 0.1 A $g^{\text{-1}}$	
		~ 201 at 0.2 A g ⁻¹	
SCNs	~ 80 at 5 A g ⁻¹ after 5000cycles	${\sim}183$ at 0.5 A g $^{-1}$	[53]
		~ 167 at 1 A g ⁻¹	
		\sim 126 at 2 A g ⁻¹	
		~604 at 0.1 A g ⁻¹	
		${\sim}550$ at 0.2 A $g^{\text{-1}}$	
Sb@Cu ₁₅ Si ₄	${\sim}250.2$ at 0.2 A g $^{\text{-1}}$ after	~495 at 0.5 A g ⁻¹	[54]
NW	1250cycles	~321 at 1 A g ⁻¹	
		${\sim}228.4$ at 2 A $g^{\text{-1}}$	
		${\sim}104.9$ at 4 A g $^{-1}$	
		~274.6 at 0.05A g-1	
		~264.2 at 0.1A g-1	
NS-SGNR	~224 at 0.5A g-1 after 500cycles	~257.5 at 0.2A g-1	[55]
		~248.3 at 0.5A g-1	
		~237.4 at 1A g-1	
		~211.7 at 2A g-1	
		~239 at 0.1 A g ⁻¹	
		~200 at 0.2 A g ⁻¹	
QLGC	~200at 0.1 A g ⁻¹ after 100cycles	~108at 0.5 A g ⁻¹	[56]
		~63 at 1 A g ⁻¹	
		\sim 28.4 at 2 A g ⁻¹	
		${\sim}500$ at 0.1 A g ^-1	

		${\sim}430$ at 02 A $g^{\text{-1}}$	
		${\sim}373$ at 0.3 A g $^{-1}$	
NP-Sb	\sim 318 at 0.1 A g ⁻¹ after 50cycles	${\sim}312$ at 0.4 A g $^{-1}$	[57]
		~265 at 0.5 A g ⁻¹	
		${\sim}362$ at 0.1 A g $^{-1}$	
		\sim 314 at 02 A g ⁻¹	
Defect-rich C	\sim 321 at 0.05 A g ⁻¹ after	${\sim}267$ at 0.5 A g $^{-1}$	[58]
	400cycles	~240 at 1 A g ⁻¹	
		~215 at 1 A g ⁻¹	
		${\sim}437$ at 0.1 A g $^{-1}$	
		~400 at 02 A g ⁻¹	
Sb ₂ O ₃ @PCN	\sim 3437 at 0.1 A g ⁻¹ after 50cycles	${\sim}337$ at 0.5 A g $^{-1}$	[59]
		~210 at 1 A g ⁻¹	
		${\sim}501$ at 0.1 A g $^{-1}$	
		\sim 480 at 02 A g ⁻¹	
Sb@CTF-NC	\sim 440 at 0.05 A g ⁻¹ after	${\sim}402$ at 0.5 A g $^{-1}$	
	2000cycles	~351 at 1 A g ⁻¹	[60]
		~232 at 2 A g ⁻¹	
		${\sim}580.8$ at 0.1 A g $^{\text{-1}}$	
		${\sim}540.6$ at 0.2 A g $^{-1}$	
Sb ₃ @HCNS	\sim 382 at 2 A g ⁻¹ after 1000 cycles	~477.5 at 0.5 A g ⁻¹	The
		~413.0 at 1 A g ⁻¹	work
		\sim 325 at 2 A g ⁻¹	
		${\sim}215.5$ at 4 A g $^{-1}$	